NSN 5961-01-598-8209

Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-598-8209 **Inclosure Material:** Plastic **Function For Which Designed:** Rectifier **Mounting Facility Quantity: Mounting Method:** Unthreaded hole **Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 1200.0 repetitive peak reverse voltage **Maximum Operating Tempurature Per Measurement Point:** 175.0 degrees celsius ambient air **Special Features:** Ave. Rectified forward current: 30a at 78 degrees c; max. Power dissipation: 125w; avalanche energy: 125w; hyperfast diode w/soft recovery characteristics; half recovery time of ultrafast diodes; used as freewheeling/clamping diode and rectifier in variety of frequency switching power supplies **Terminal Type And Quantity:** 2 uninsulated wire lead Shelf Life: N/a **Unit Of Measure: Demilitarization:** No Fiig: A110a0